

2SA984, 984K



2003A

PNP/NPN Epitaxial Planar
Silicon Transistors

2SC2274, 2274K

Low Frequency Power Amp Applications

©465F

Features

- . High breakdown voltage ($V_{CE0} \geq 50/80V$).
- . High current ($I_C = 500mA$).
- . Low saturation voltage.

(): 2SA984, 984K

Absolute Maximum Ratings at Ta=25°C		A984, C2274	A984K, C2274K	unit
Collector to Base Voltage	V_{CBO}	(-) 60	(-) 100	V
Collector to Emitter Voltage	V_{CEO}	(-) 50	(-) 80	V
Emitter to Base Voltage	V_{EBO}		(-) 5	V
Collector Current	I_C		(-) 500	mA
	i_{cp}		(-) 800	mA
Collector Dissipation	P_C		600	mW
Junction Temperature	T_j		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

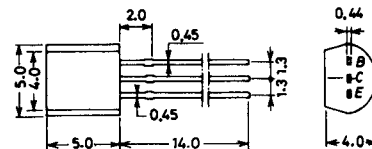
Electrical characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = (-) 40V, I_E = 0$			(-) 1.0	uA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-) 4V, I_C = 0$			(-) 1.0	uA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = (-) 5V, I_C = (-) 50mA$	60*		320*	
	$h_{FE(2)}$	$V_{CE} = (-) 5V, I_C = (-) 400mA$ (pulse)	35			
G-B Product	f_T	$V_{CE} = (-) 10V, I_C = (-) 10mA$		120		MHz
Output Capacitance	C_{ob}	$V_{CB} = (-) 10V, f = 1MHz$		(9)		pF
				5		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-) 400mA, I_B = (-) 40mA$		(-0.25)	(-0.6)	V
B-E Saturation Voltage	$V_{BE(sat)}$	" "		0.2	0.6	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-) 10uA, I_E = 0$				V
		A984, C2274			(-) 60	V
		A984K, C2274K			(-) 100	V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-) 1mA, R_{BE} = open$				V
		A984, C2274			(-) 50	V
		A984K, C2274K			(-) 80	V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-) 10uA, I_C = 0$			(-) 5	V

* The 2SA984, K, 2SC2274, K are classified by 50mA h_{FE} as follows.

60	D	120	100	E	200	160	F	320
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Case Outline 2003A (unit:mm)



JEDEC: TO-92 B: Base
EIAJ: SC-43 C: Collector
SANYO: NP E: Emitter

For details, refer to the description of the 2SC2274, 2274K.

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